L Number	Hits	Search Text	DB	Time stamp
85	0	((two or first or second) near2 ((tft or (thin	USPAT;	2004/09/20
	_	near film near transistor)) with active with	US-PGPUB;	08:30
		channel) and ((channel with thickness with	EPO; JPO;	,
		different with (tft or (thin near film near	DERWENT;	
		transistor)))))	IBM_TDB	
86	22	(tft or (thin near film near transistor)) with	USPAT;	2004/09/20
		different with (channel near5 (thick or	US-PGPUB;	08:31
		thickness))	EPO; JPO;	00.01
		tilletile33))	DERWENT;	
			IBM_TDB	
87	15	/4ff or /thin maar film maar transistor\\	USPAT;	2004/09/20
87	15	(tft or (thin near film near transistor))	1	
		near10 different near10 (channel near5	US-PGPUB;	08:32
1		(thick or thickness))	EPO; JPO;	
			DERWENT;	
	-		IBM_TDB	
88	0	((first or second or two) near2 (tft or (thin	USPAT;	2004/09/20
		near film near transistor))) near10 different	US-PGPUB;	08:36
		near10 (channel near5 (thick or thickness))	EPO; JPO;	
•			DERWENT;	
		·	IBM_TDB	
89	11	((first or second or two) near2 (tft or (thin	USPAT;	2004/09/20
		near film near transistor))) near10 (channel	US-PGPUB;	08:41
		near2 (thick or thickness))	EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
90	2	koo and park and lee and (channel near2	USPAT;	2004/09/20
		(thick or thicker or thin or thinner or	US-PGPUB;	08:42
		thickness))	EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
91	2752	(tft or (thin adj film adj transistor)) with	USPAT;	2004/09/20
١	2,02	(channel near2 (thick or thicker or thin or	US-PGPUB:	08:42
		thinner or thickness))	EPO; JPO;	00:42
		tilliner of tillckiless))	DERWENT;	
			1	
	2670	(Aft on (Ahin odi film odi tuonoistor)) nondo	IBM_TDB	2004/00/20
92	2670	(tft or (thin adj film adj transistor)) near10	USPAT;	2004/09/20
		(channel near2 (thick or thicker or thin or	US-PGPUB;	08:43
		thinner or thickness))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
93	1059	((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:43
		(channel near2 (thick or thicker or thin or	EPO; JPO;	
		thinner or thickness))	DERWENT;	
			IBM_TDB	
94	508	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:44
		(channel near2 (thick or thicker or thin or	EPO; JPO;	
	:	thinner or thickness))).ti,ab,clm.	DERWENT;	
		,,,,,	IBM_TDB	

95		///n av first av accord or two or n) noor2 (4ff	HCDAT.	2004/00/20
90	7	(((p or first or second or two or n) near2 (tft or (thin adj film adj transistor))) near10	USPAT; US-PGPUB;	2004/09/20 08:46
		, ,	1	00:40
		(channel near2 (thick or thicker or thinner or thickness))).ti,ab,clm.	EPO; JPO; DERWENT;	
		or thickness///.ti,ab,cilli.	IBM_TDB	
97	10	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
٠,	10	or (thin adj film adj transistor))) near10	US-PGPUB;	08:47
		(channel near2 (different or thick or thicker	EPO; JPO;	00:47
		1 -	, ,	
		or thinner or thickness))).ti,ab,clm.	DERWENT;	
96	76	(IIn or first or second or two or n) near? (46)	IBM_TDB	2004/09/20
90	76	(((p or first or second or two or n) near2 (tft	USPAT;	08:50
		or (thin adj film adj transistor))) near10	US-PGPUB;	00:30
		(channel near2 (different or thick or thicker	EPO; JPO;	
		or thinner or thickness)))	DERWENT;	
	•	///	IBM_TDB	2004/00/00
98	0	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:50
		(channel near2 (different near thickness)))	EPO; JPO;	
			DERWENT;	
	•	(//	IBM_TDB	0004/00/00
99	0	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:51
		(channel near3 (different near thickness)))	EPO; JPO;	
			DERWENT;	
400			IBM_TDB	
100	0	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:51
		(channel near5 (different near thickness)))	EPO; JPO;	
			DERWENT;	
404	40	// 5. 4 I 4	IBM_TDB	
101	13	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:55
		(channel near5 ((thicker or thinner or	EPO; JPO;	
		(different near thickness)))))	DERWENT;	
400	444		IBM_TDB	0004/00/00
102	144	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:55
,		(channel near5 ((wider or higher or taller or	EPO; JPO;	
		thicker or thinner or (different near	DERWENT;	
		(thickness or dimension or height or	IBM_TDB	. •
400		width)))))		
103	29	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:56
		(channel near5 ((wider or higher or taller or	EPO; JPO;	
		thicker or thinner or (different near	DERWENT;	
		(thickness or dimension or height or	IBM_TDB	
404	_	width))))).clm.		0004/00/07
104	8	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:58
		(channel near3 (layer or region) near3	EPO; JPO;	
		((wider or higher or taller or thicker or	DERWENT;	
		thinner or (different near (thickness or	IBM_TDB	
		dimension or height or width)))))).clm.	L	

105	27	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	08:58
		(channel near3 (layer or region) near3	EPO; JPO;	
		((wider or higher or taller or thicker or	DERWENT;	
		thinner or (different near (thickness or	IBM_TDB	
		dimension or height or width)))))		2
106	24	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor)))	US-PGPUB;	08:59
		near5(channel near3 (layer or region) near3	EPO; JPO;	
		((wider or higher or taller or thicker or	DERWENT;	
		thinner or (different near (thickness or	IBM_TDB	
		dimension or height or width)))))		
107	7	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
	•	or (thin adj film adj transistor))) near5	US-PGPUB;	09:00
		(channel near3 (layer or region) near3	EPO; JPO;	03.00
	•	((wider or taller or thicker or thinner or	DERWENT;	
		(different near (thickness or dimension or	IBM_TDB	
		height or width)))))	IBM_IDB	
108	8		HEDAT.	2004/00/20
100	0	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	09:02
		(channel near3 (layer or region) near3	EPO; JPO;	
		((wider or taller or thicker or thinner or	DERWENT;	
		(different near (thickness or dimension or	IBM_TDB	
		height or width))))))		
109	1	((((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	09:02
		(channel near3 (layer or region) near3	EPO; JPO;	·
		((wider or taller or thicker or thinner or	DERWENT;	
		(different near (thickness or dimension or	IBM_TDB	
		height or width))))))) not ((((p or first or		
		second or two or n) near2 (tft or (thin adj		
		film adj transistor))) near5 (channel near3		
		(layer or region) near3 ((wider or taller or	,	
		thicker or thinner or (different near		
		(thickness or dimension or height or		
		width))))))		
110	13	(((p or first or second or two or n) near2 (tft	USPAT;	2004/09/20
		or (thin adj film adj transistor))) near10	US-PGPUB;	09:02
		(channel near5 (layer or region) near5	EPO; JPO;	
		((wider or taller or thicker or thinner or	DERWENT;	
		(different near (thickness or dimension or	IBM_TDB	
		height or width)))))	<u>-</u>	

111	5	((((p or first or second or two or n) near2 (tft or (thin adj film adj transistor))) near10 (channel near5 (layer or region) near5 ((wider or taller or thicker or thinner or (different near (thickness or dimension or height or width))))))) not (((p or first or second or two or n) near2 (tft or (thin adj film adj transistor))) near10 (channel near3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:03
		(layer or region) near3 ((wider or taller or thicker or thinner or (different near (thickness or dimension or height or width)))))))		
112	489	(different near channel near (width or thickness))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:03
113	77	(different near channel near (width or thickness)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:03
114	3	(tft or (thin adj film adj transistor)).clm. and (different near channel near (width or thickness)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:05
115	5	(tft or (thin adj film adj transistor)).clm. and (different near2 channel near2 (width or thickness)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:06
116	3	((tft or (thin adj film adj transistor)) with (different near channel near (width or thickness))).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:25
117	0	(((tft or (thin adj film adj transistor)) with (different near channel near (width or thickness))) with (thicker or wider or thinner)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:14
118	0	((tft or (thin adj film adj transistor)) with (different near channel near (width or thickness))).ti,ab,clm. and (channel with (wider or thicker or thinner)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:15
119	2	((tft or (thin adj film adj transistor)) with (different near channel near (width or thickness))) and (channel with (wider or thicker or thinner))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 09:15